

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

KEY PARAMETERS

V_{DRM}	4800V
$I_{T(AV)}$	1088A
I_{TSM}	15000A
dV/dt^*	300V/μs
dI/dt	200A/μs

*Higher dV/dt selections available

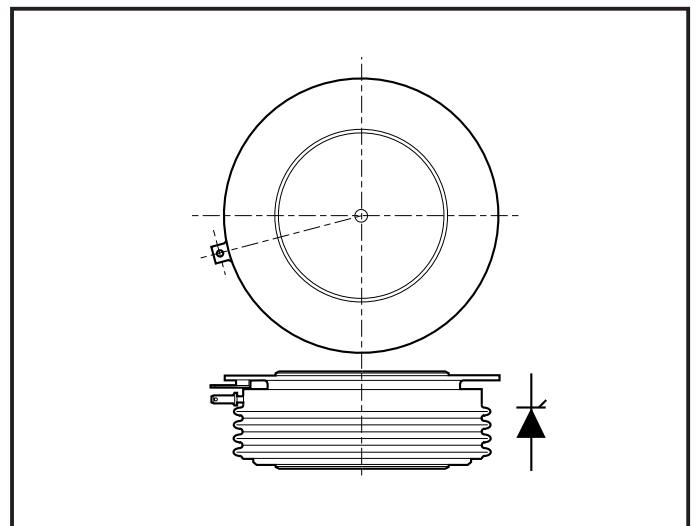
FEATURES

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM} V	Conditions
DCR1279SD48	4800	$T_{vj} = 0^\circ$ to 125° C, $I_{DRM} = I_{RRM} = 150$ mA, V_{DRM}^* V_{RRM} $t_p = 10$ ms, V_{DSM} & $V_{RSM} =$ V_{DRM} & $V_{RRM} + 100$ V respectively
DCR1279SD47	4700	
DCR1279SD46	4600	
DCR1279SD45	4500	
DCR1279SD44	4400	

Lower voltage grades available.



Outline type code: D.

See package outline for further information.

CURRENT RATINGS

$T_{case} = 60^\circ$ C unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load,	1088	A
$I_{T(RMS)}$	RMS value	-	1709	A
I_T	Continuous (direct) on-state current	-	1574	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	762	A
$I_{T(RMS)}$	RMS value	-	1197	A
I_T	Continuous (direct) on-state current	-	1034	A

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CURRENT RATINGS

$T_{case} = 80^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load,	860	A
$I_{T(RMS)}$	RMS value	-	1350	A
I_T	Continuous (direct) on-state current	-	1055	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	590	A
$I_{T(RMS)}$	RMS value	-	930	A
I_T	Continuous (direct) on-state current	-	860	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}\text{C}$	12.0	kA
I^2t	I^2t for fusing	$V_R = 50\% V_{RRM}$ - 1/4 sine	0.72×10^6	A^2s
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}\text{C}$	15.0	kA
I^2t	I^2t for fusing	$V_R = 0$	1.12×10^6	A^2s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.020	$^{\circ}\text{C/W}$
		Single side cooled	Anode dc	-	0.036	$^{\circ}\text{C/W}$
			Cathode dc	-	0.044	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 22.0kN with mounting compound	Double side	-	0.004	$^{\circ}\text{C/W}$
			Single side	-	0.008	$^{\circ}\text{C/W}$
T_{vj}	Virtual junction temperature	On-state (conducting)	-	135	$^{\circ}\text{C}$	
		Reverse (blocking)	-	125	$^{\circ}\text{C}$	
T_{stg}	Storage temperature range		-55	125	$^{\circ}\text{C}$	
-	Clamping force		22.0	24.0	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	150	mA	
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$. Gate open circuit.	-	300	V/ μ s	
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A Gate source 10V, 5 Ω $t_r \leq 0.5\mu$ s, $T_j = 125^{\circ}C$	Repetitive 50Hz	-	100	A/ μ s
			Non-repetitive	-	200	A/ μ s
$V_{T(TO)}$	Threshold voltage	At $T_{vj} = 125^{\circ}C$	-	1.14	V	
r_T	On-state slope resistance	At $T_{vj} = 125^{\circ}C$	-	0.587	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15 Ω $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	-	2.5	μ s	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	300	1000	mA	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$	-	500	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	4.0	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	400	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	10	A
P_{GM}	Peak gate power	See table, fig.4	150	W
$P_{G(AV)}$	Mean gate power		5	W

CURVES

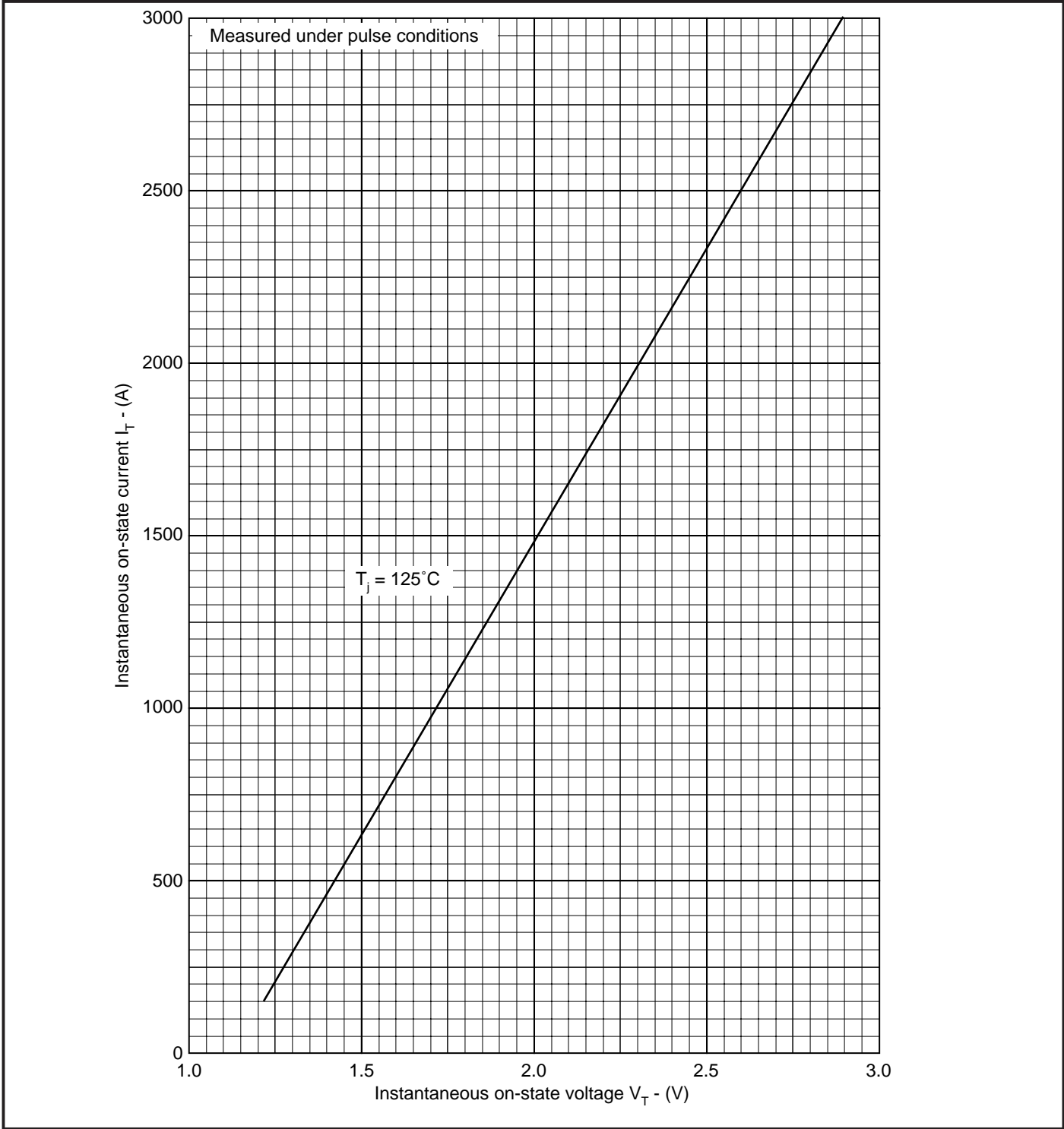


Fig.1 Maximum (limit) on-state characteristics

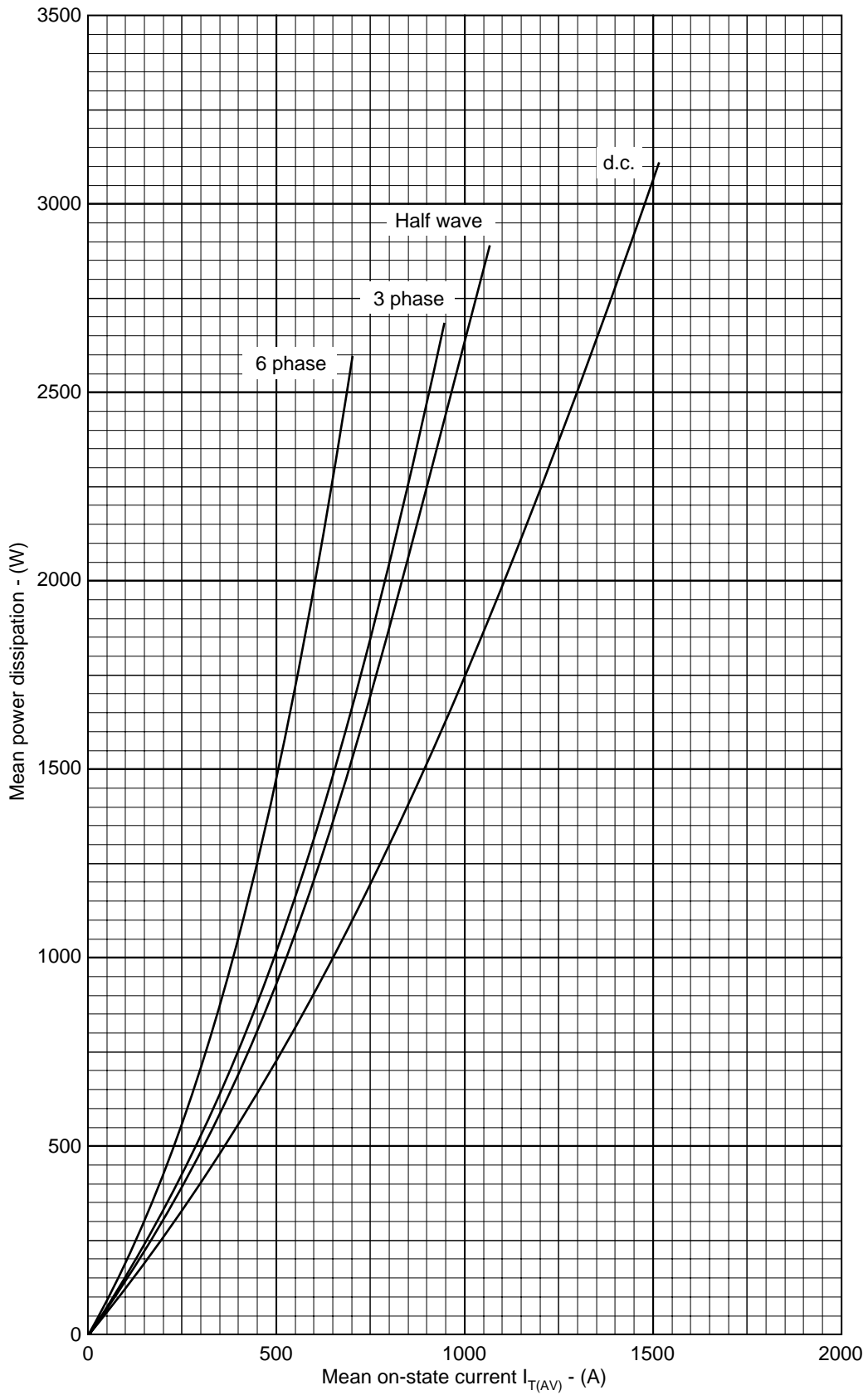


Fig.2 Dissipation curves

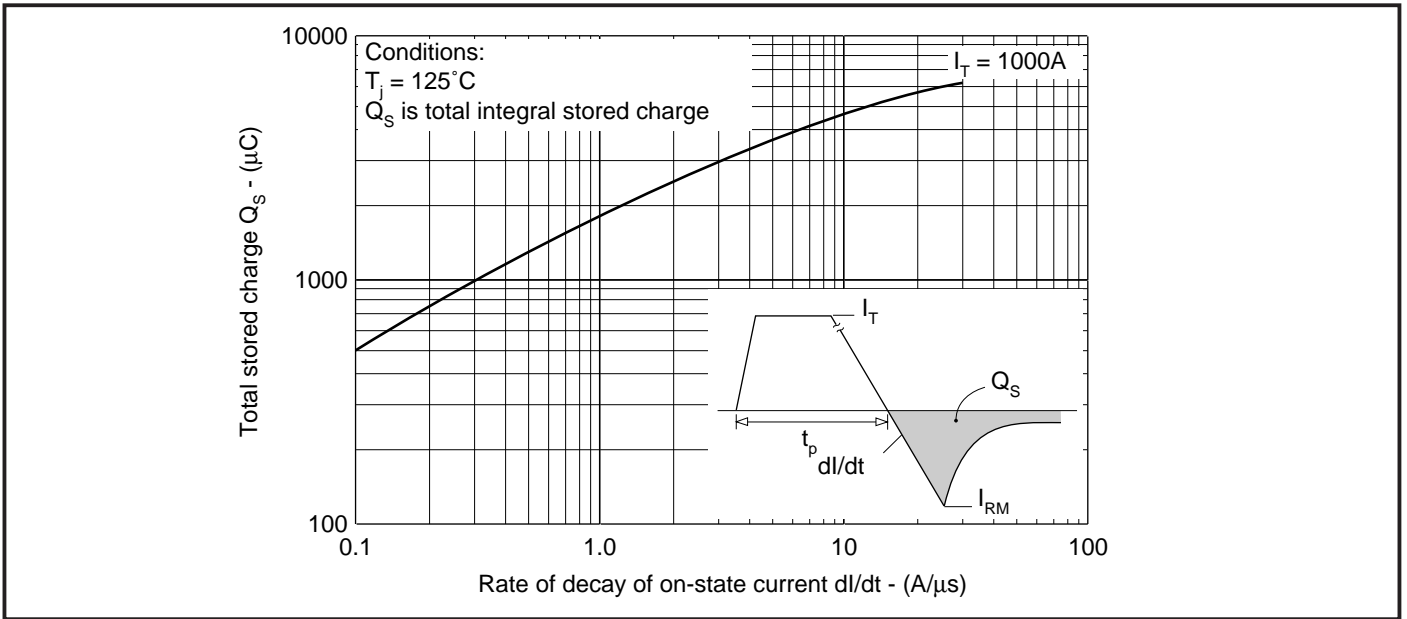


Fig.3 Stored charge

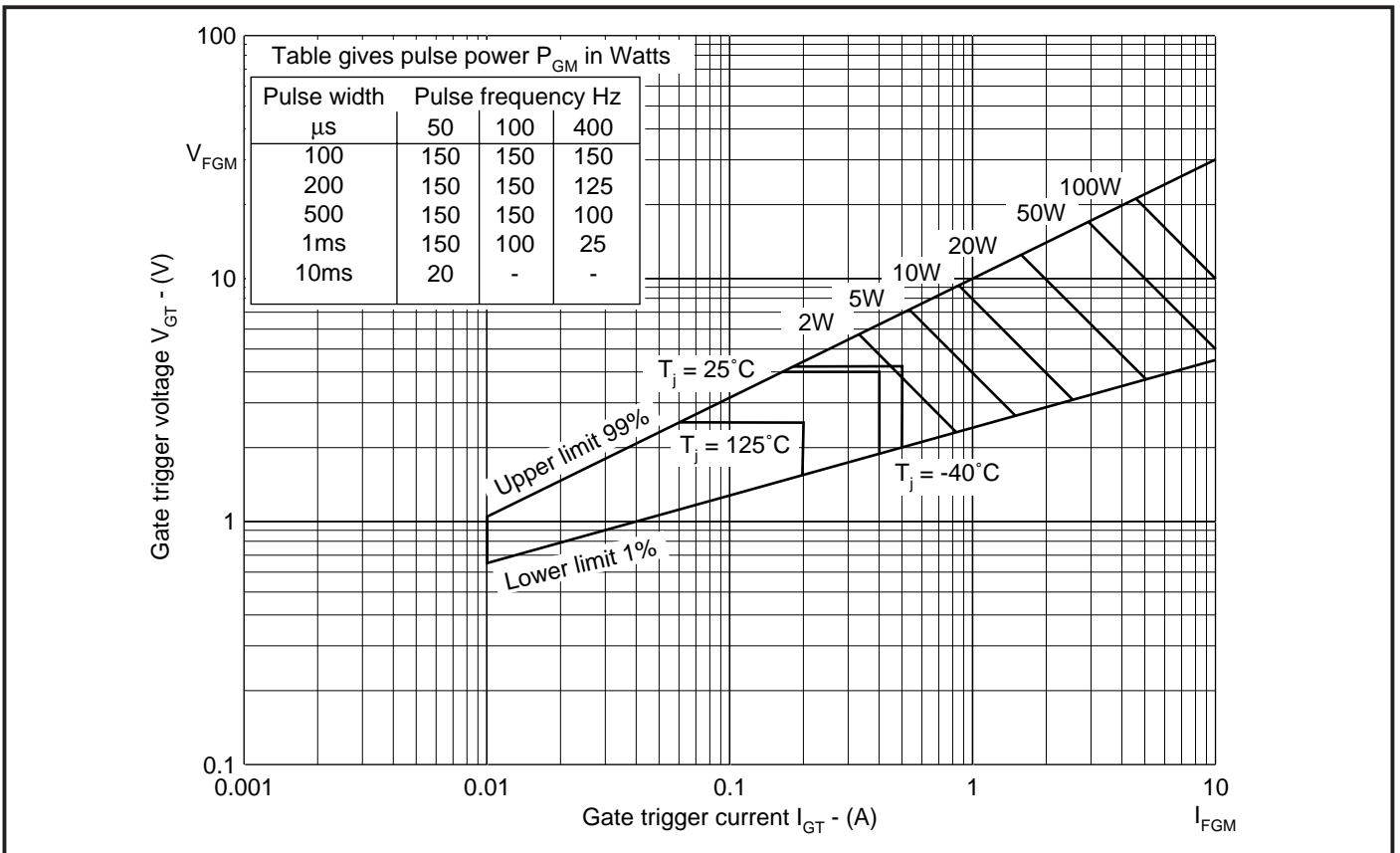


Fig.4 Gate characteristics

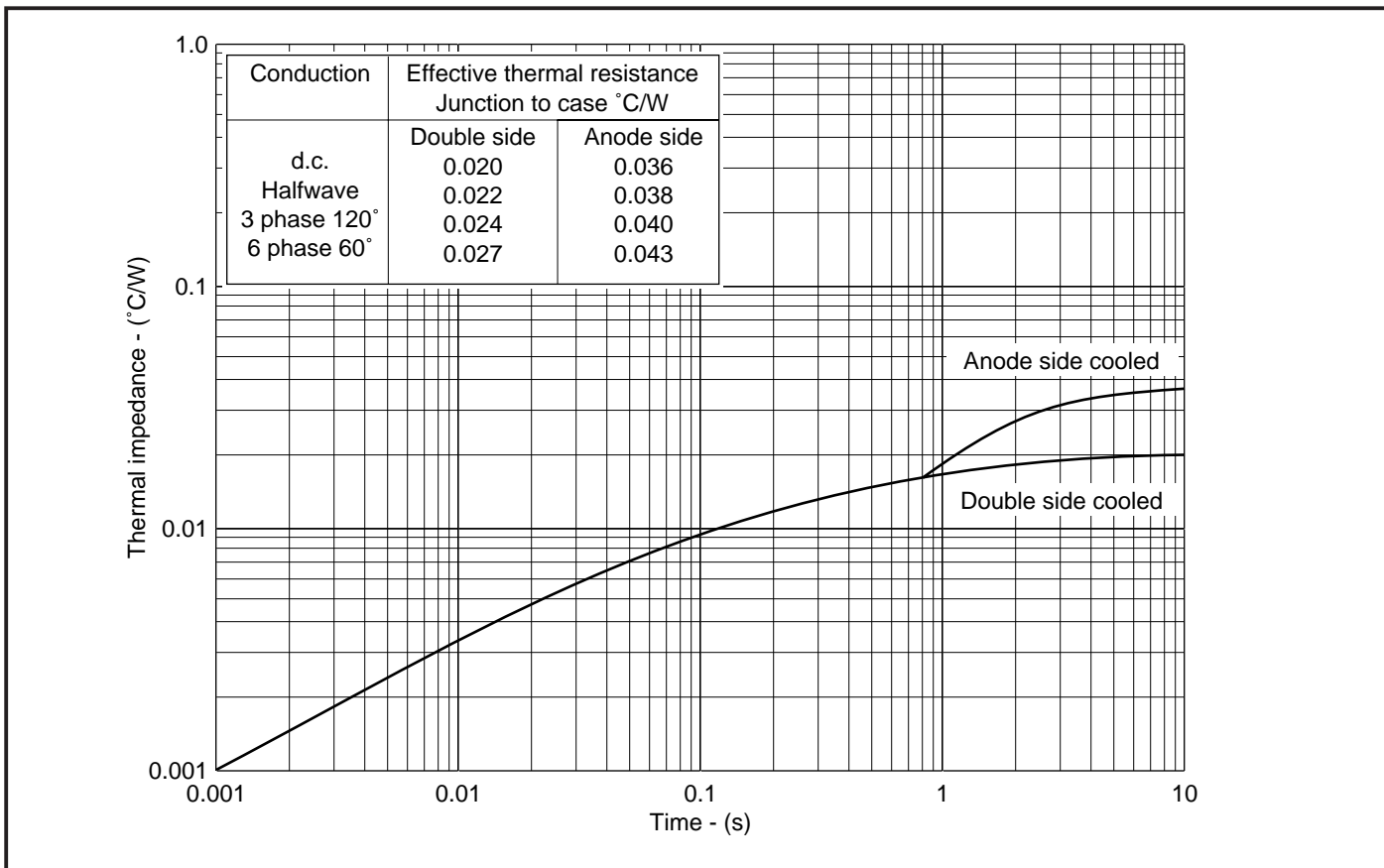


Fig.5 Maximum (limit) transient thermal impedance - junction to case

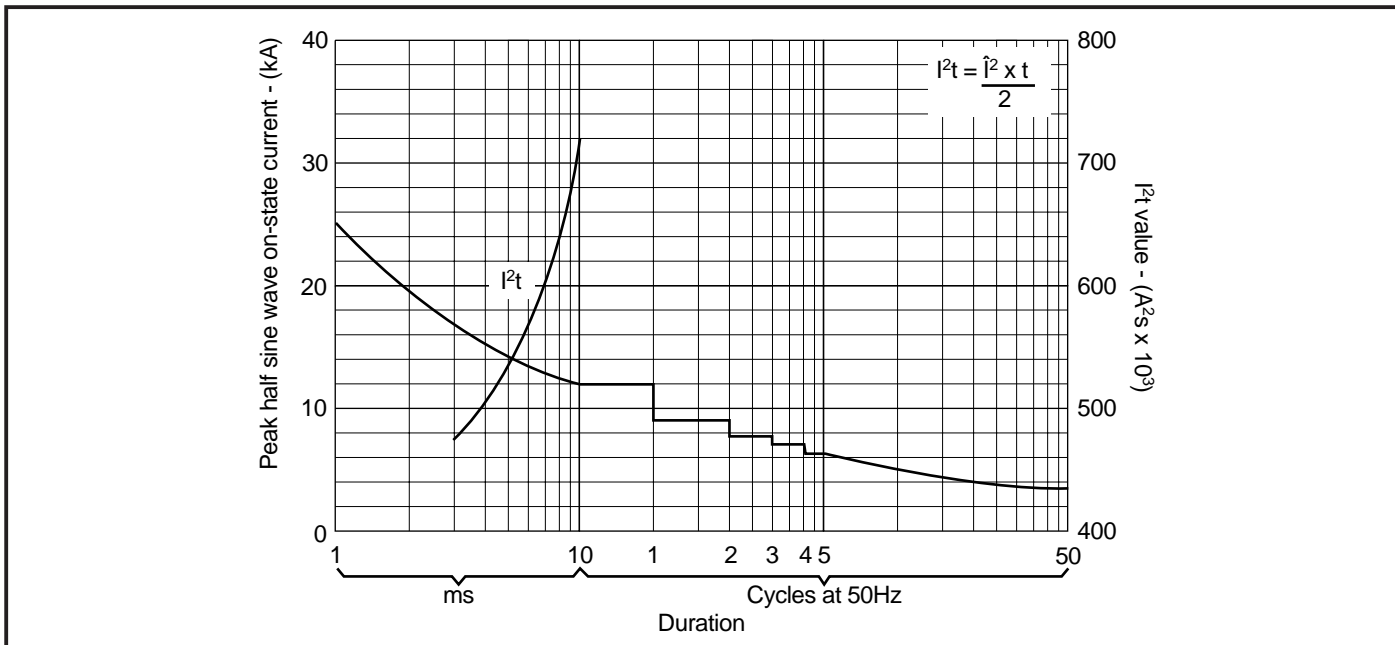
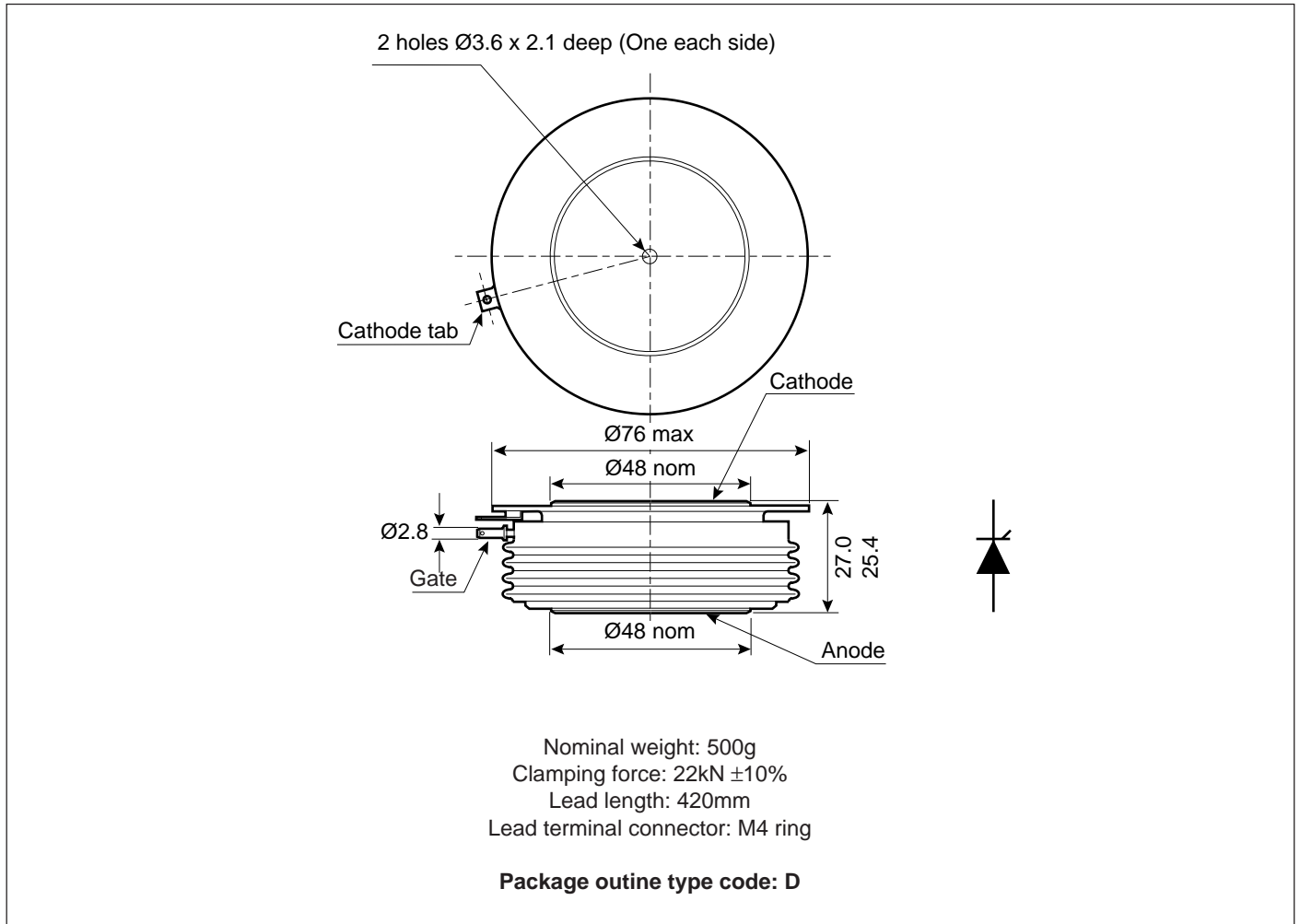


Fig.6 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at $T_{case} 125^\circ C$)

DCR1279SD

PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



ASSOCIATED PUBLICATIONS

Title	Application Note Number
Calculating the junction temperature or power semiconductors	AN4506
Gate triggering and the use of gate characteristics	AN4840
Recommendations for clamping power semiconductors	AN4839
The effect of temperature on thyristor performance	AN4870
Thyristor and diode measurement with a multi-meter	AN4853
Turn-on performance of thyristors in parallel	AN4999
Use of V_{TO} , r_T on-state characteristic	AN5001

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or the factory.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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